

Investigation of avalanche photodiodes after irradiation with neutrons up to 5×10^{14} n/cm²

Content

Results on the radiation hardness of avalanche photodiodes to fast neutrons are presented. APDs from Hamamatsu were irradiated with reactor neutrons up to 1 MeV equivalent fluence of 5×10^{14} n/cm². The effects of this radiation on many parameters such as gain, intrinsic dark current, quantum efficiency, noise and capacitance for these devices are shown and discussed.

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